

CES2310L

30V ▲ 24mΩ ▲ 4.8A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

SOT23 package ▲ MSL 3

Super high dense cell density for extremely low $R_{DS(ON)}$

Rugged and reliable






MAXIMUM RATINGS

Parameter ($T_A = 25^\circ\text{C}$, unless otherwise noted)		Characteristics
Drain-Source Voltage	V_{DS}	30V
Gate-Source Voltage	V_{GS}	$\pm 12\text{V}$
Continuous Drain Current at $T_A = 25^\circ\text{C}$	I_D	4.8A
Pulsed Drain Current ^{Note 1}	I_{DM}	20A
Maximum Power Dissipation	P_D	1.25W
Operating and Storage Temperature Range	T_J, T_{STG}	-55°C to $+150^\circ\text{C}$

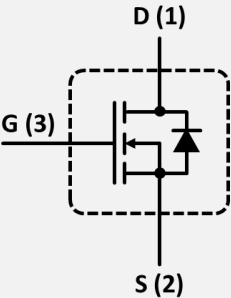
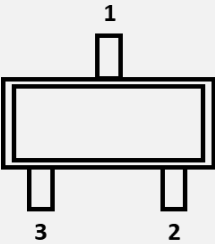
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient ^{Note 2}	R_{TH_JA}	100°C/W

APPLICATIONS

Battery Pack	DC Fan	Load Switches	Power Banks	USB Storage
				

PIN DESCRIPTION

Circuit Diagram	Outline - Top View	Pin No.	Description
		1 2 3	Drain Source Gate

ELECTRICAL CHARACTERISTICS ▲ $T_A = 25^\circ\text{C}$, unless otherwise noted

Item	Condition	Symbol	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	30			V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I_{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 12V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -12V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics ^{Note 3}						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	$V_{GS(th)}$	0.4		1	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 4.8A$	$R_{DS(ON)}$		24	34	m Ω
Static Drain-Source On-Resistance	$V_{GS} = 4.5V, I_D = 4A$	$R_{DS(ON)}$		26	40	m Ω
Static Drain-Source On-Resistance	$V_{GS} = 2.5V, I_D = 2A$	$R_{DS(ON)}$		30	45	m Ω
Static Drain-Source On-Resistance	$V_{GS} = 1.8V, I_D = 1A$	$R_{DS(ON)}$		34	60	m Ω
Dynamic Characteristics ^{Note 4}						
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	C_{ISS}		520		pF
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	C_{OSS}		85		pF
Reverse Transfer Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	C_{RSS}		60		pF
Switching Characteristics ^{Note 4}						
Turn-On Delay Time	$V_{DD} = 15V, V_{GS} = 4.5V, I_D = 4.8A, R_{G(ext)} = 10\Omega$	$t_{D(ON)}$		9		ns
Turn-On Rise Time	$V_{DD} = 15V, V_{GS} = 4.5V, I_D = 4.8A, R_{G(ext)} = 10\Omega$	t_R		6		ns
Turn-Off Delay Time	$V_{DD} = 15V, V_{GS} = 4.5V, I_D = 4.8A, R_{G(ext)} = 10\Omega$	$t_{D(OFF)}$		44		ns
Turn-Off Fall Time	$V_{DD} = 15V, V_{GS} = 4.5V, I_D = 4.8A, R_{G(ext)} = 10\Omega$	t_F		10		ns
Total Gate Charge	$V_{DS} = 15V, V_{GS} = 4.5V, I_D = 4.8A$	Q_G		10		nC
Gate Source Charge	$V_{DS} = 15V, V_{GS} = 4.5V, I_D = 4.8A$	Q_{GS}		1		nC
Gate Drain Charge	$V_{DS} = 15V, V_{GS} = 4.5V, I_D = 4.8A$	Q_{GD}		3		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^{Note 2}		I_S			1.2	A
Drain-Source Diode Forward Voltage ^{Note 3}	$V_{GS} = 0V, I_S = 1A$	V_{SD}			1	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, $t \leq 10$ sec
- 3: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 4: Guaranteed by design, not subject to production testing.

REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 1 • Output Characteristics

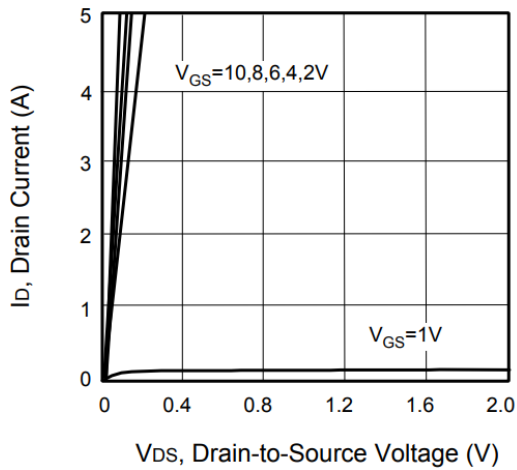


Fig. 2 • Transfer Characteristics

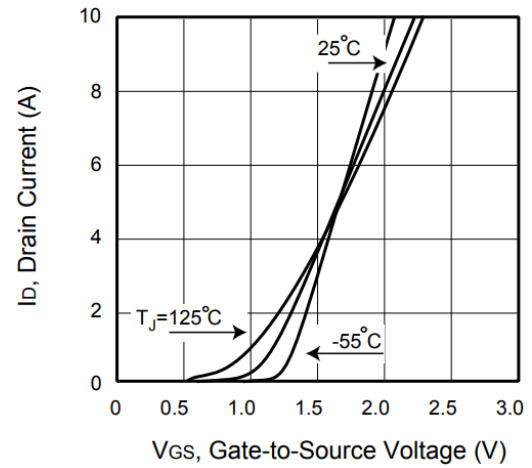


Fig. 3 • Capacitance

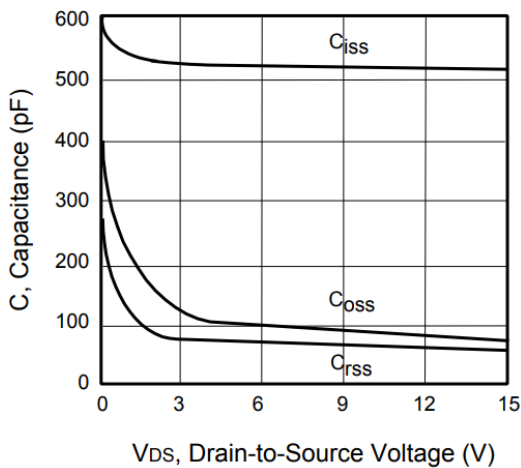


Fig. 4 • On-Resistance Variation with Temperature

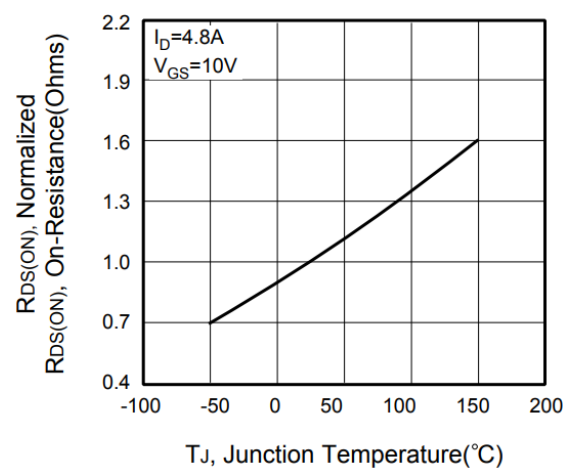


Fig. 5 • Gate Threshold Variation with Temperature

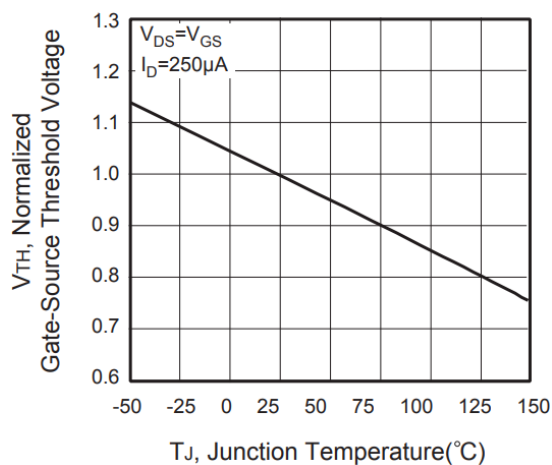
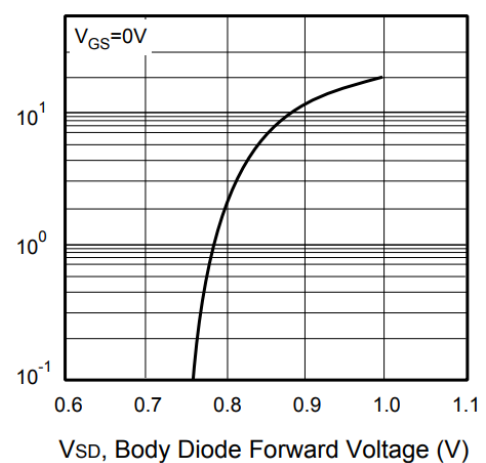


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

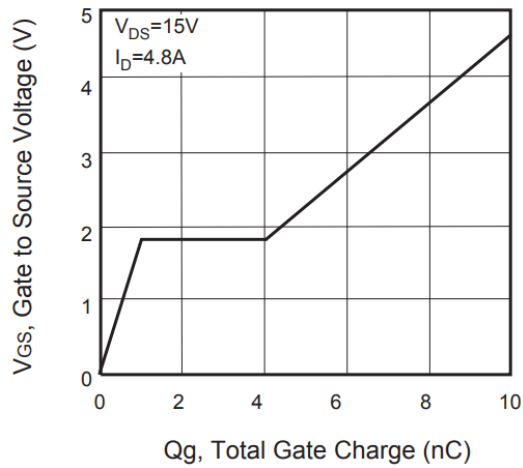


Fig. 8 • Maximum Safe Operating Area

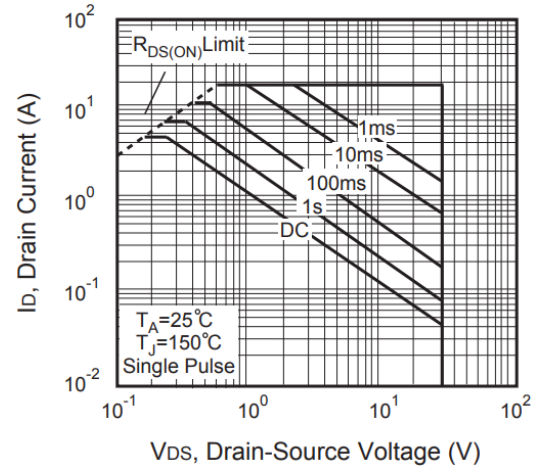


Fig. 9 • Breakdown Voltage Variation vs. Temperature

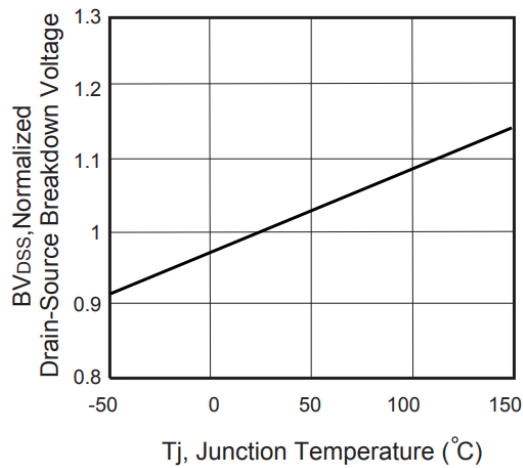


Fig. 10 • Switching Test Circuit

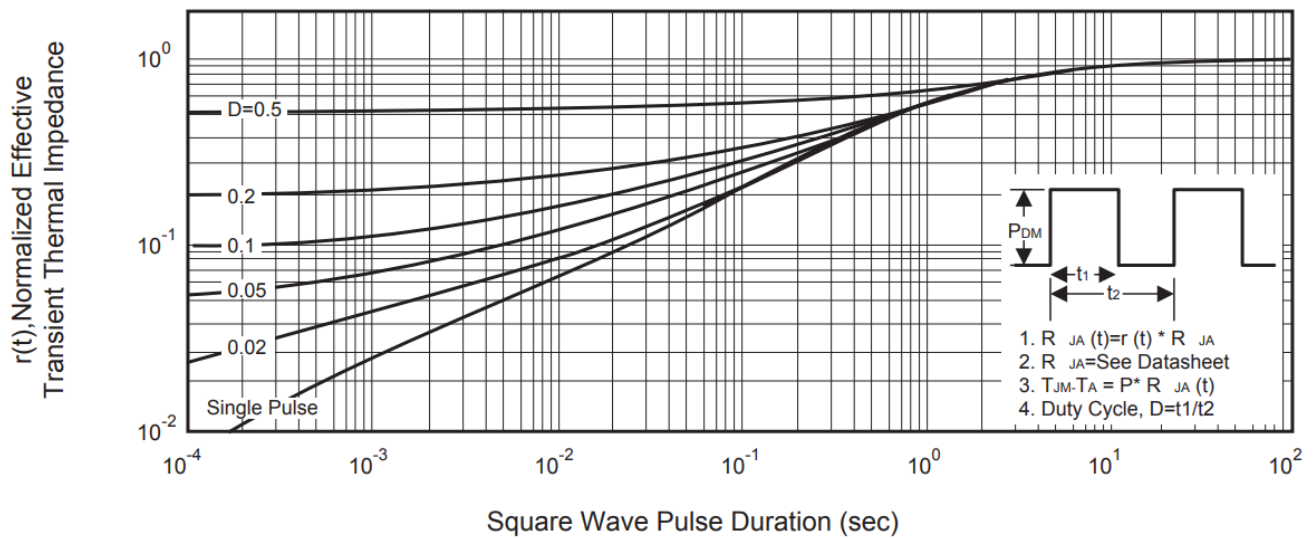


Fig. 11 • Switching Waveforms

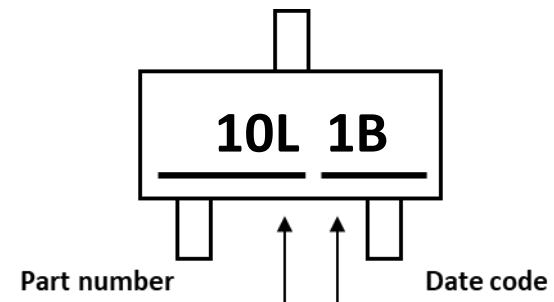


REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE

Fig. 12 ▪ Normalized Thermal Transient Impedance Curve

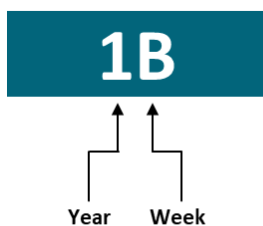


PART MARKING



DATE CODE

Example: 1B



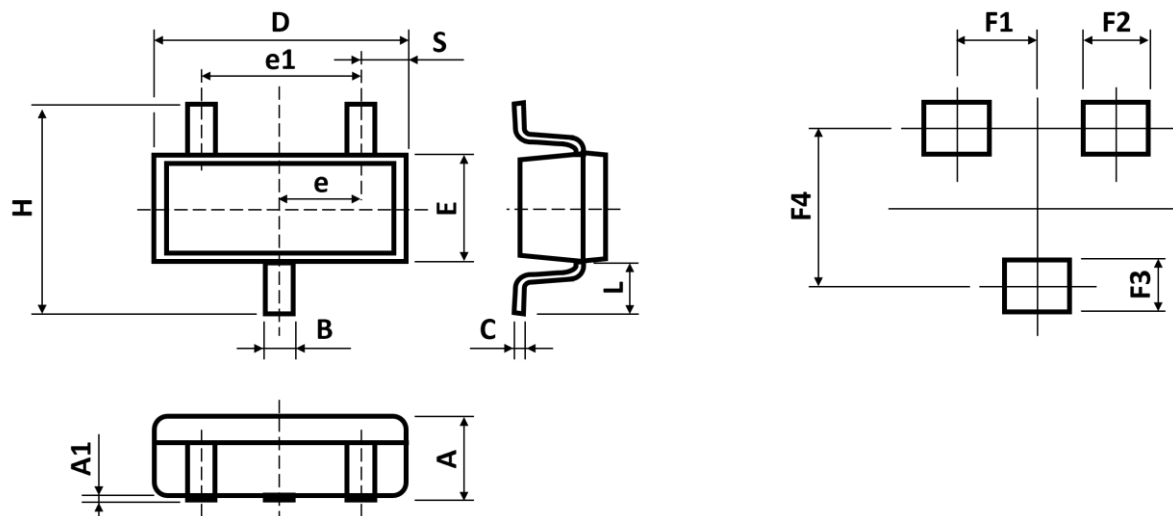
Coding list for „Week“

A	B	C	D	E	F	G	H	I
1-2	3-4	5-6	7-8	9-10	11-12	13-14	15-16	17-18
J	K	L	M	N	O	P	Q	R
19-20	21-22	23-24	25-26	27-28	29-30	31-32	33-34	35-36
S	T	U	V	W	X	Y	Z	
37-38	39-40	41-42	43-44	45-46	47-48	49-50	51-52	

Coding list for „Year“

0	1	2	3	4
2020	2021	2022	2023	2024
5	6	7	8	9
2025	2026	2027	2028	2029

PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
A	0.890	-	1.250
A1	0.000	-	0.100
B	0.300	-	0.500
C	0.085	-	0.200
D	2.720	-	3.040
E	1.400	-	1.800

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	0.950	-
F2	-	0.760	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
e	0.95 BSC		
e1	1.780	-	2.180
H	2.500	-	3.100
L	0.550 REF		
S	0.410	-	0.610

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F3	-	0.760	-
F4	-	2.290	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

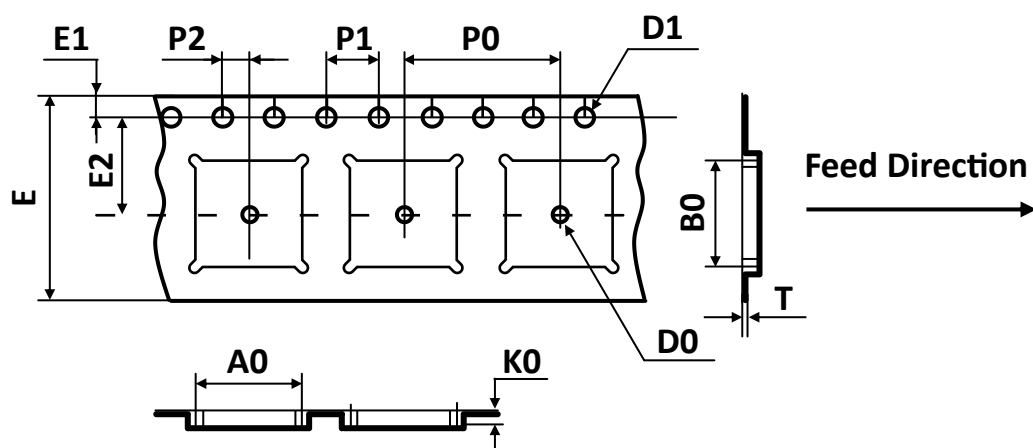
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.
CES2310L	SOT23	7" Reel	3,000pcs	15,000pcs

REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	H	K	S
8mm	Ø180	Ø178.00 ±1.00	Ø54.00 ±0.50	1.20 ±0.20	20.00 ±1.00	13.30 ±0.30	3.00 ±1.00

TAPE DIMENSIONS ▲ All dimensions in mm



Package	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT23	3.25 ±0.10	3.25 ±0.10	1.35 ±0.10	1.00 ±0.10	1.50 ±0.10	8.00 ±0.10	1.75 ±0.10	3.50 ±0.10	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.02

Note: All dimensions meet EIA-481-D requirements.

RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ Refer to JEDEC J-STD-020E

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s \text{ min}}$	100 °C	150 °C
Preheat temperature max.	$T_{s \text{ max}}$	150 °C	200 °C
Preheat time t_s from $T_{s \text{ min}}$ to $T_{s \text{ max}}$	t_s	120 seconds	120 seconds
Ramp-up rate (T_L to T_p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t_L maintained above T_L	t_L	150 seconds max.	150 seconds max.
Peak package body temperature	T_p	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t_p	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes

REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website www.mgt.co.com.